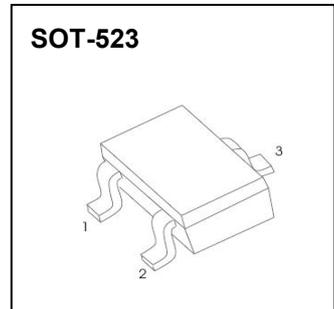


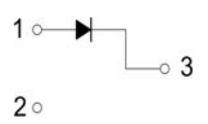
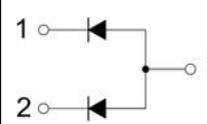
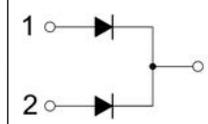
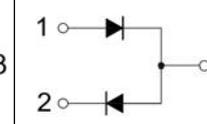
### Plastic-Encapsulate Diode

#### SWITCHING DIODE

#### FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



MMBD4448HT	MMBD4448HTA	MMBD4448HTC	MMBD4448HTS
			
MARKING:A3	MARKING:A6	MARKING:A7	MARKING:AB

#### Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>a</sub>=25 °C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	100	V
Peak Repetitive Peak Reverse Voltage	V <sub>RRM</sub>		
Working Peak Reverse Voltage	V <sub>RWM</sub>	80	V
DC Blocking Voltage	V <sub>R</sub>		
RMS Reverse Voltage	V <sub>R(RMS)</sub>	57	V
Forward Continuous Current	I <sub>FM</sub>	500	mA
Average Rectified Output Current	I <sub>O</sub>	250	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I <sub>FSM</sub>	2.0	A
Power Dissipation	P <sub>d</sub>	150	mW
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Storage Temperature	T <sub>STG</sub>	-55 ~+150	°C

#### Electrical Ratings @T<sub>a</sub>=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V <sub>R</sub>	80			V	I <sub>R</sub> =2.5 μA
Forward voltage	V <sub>F1</sub>	0.62		0.72	V	I <sub>F</sub> =5mA
	V <sub>F2</sub>			0.855	V	I <sub>F</sub> =10mA
	V <sub>F3</sub>			1.0	V	I <sub>F</sub> =100mA
	V <sub>F4</sub>			1.25	V	I <sub>F</sub> =150mA
Reverse current	I <sub>R1</sub>			0.1	μA	V <sub>R</sub> =70V
	I <sub>R2</sub>			25	nA	V <sub>R</sub> =20V
Capacitance between terminals	C <sub>T</sub>			3.5	pF	V <sub>R</sub> =6V, f=1MHz
Reverse recovery time	t <sub>rr</sub>			4	ns	I <sub>F</sub> =I <sub>R</sub> =10mA I <sub>rr</sub> =0.1I <sub>R</sub> , R <sub>L</sub> =100Ω

## Typical Characteristics

